

1200V Silicon Carbide Schottky Diode

DESCRIPTION :

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- Excellent Surge Current Capability
- Positive Temperature Coefficient on VF
- High frequency operation
- RoHS Compliant

V_{RRM}	1200V
I_F	2A ($T_C=160^\circ\text{C}$)
Q_C	16nC

TYPICAL APPLICATIONS :

- SMPS, PFC
- UPS
- Motor drivers



SMA

MAXIMUM RATINGS (at $T_J = 25^\circ\text{C}$, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Continuous Forward Current	$T_C=25^\circ\text{C}$ $T_C=160^\circ\text{C}$	I_F	8 2	A
Non-Repetitive Forward Surge Current	$T_C=25^\circ\text{C}$, $t_p=10\text{ms}$, Half sine pulse	I_{FSM}	24	A
i^2t value	$T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	$\int i^2 dt$	2.9	A^2S
Power dissipation	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	P_{tot}	50 22	W
Operation Junction temperature		T_j	-55~+175	$^\circ\text{C}$
Storage temperature		T_{STG}	-55~+175	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Typical	Unit
Thermal resistance, junction - case		$R_{th(j-c)}$	2.98	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
DC Blocking Voltage	V_{DC}	1200			V
Forward Voltage IF = 2A, Tc =25°C IF = 2A, Tc =175°C	V_F		1.4 2.1		V
Reverse Current VR = 1200V, Tc =25°C VR = 1200V, Tc =175°C	I_R		1 2		uA
Total Capacitive Charge VR = 800V	Q_C		16		nC
Total capacitance VR = 1V, f =1MHz VR = 400V, f =1MHz VR = 800V, f =1MHz	C		112 17 14		pF
Capacitance Stored Energy VR = 800 V	E_c		5.1		uJ

TYPICAL CHARACTERISTICS CURVES

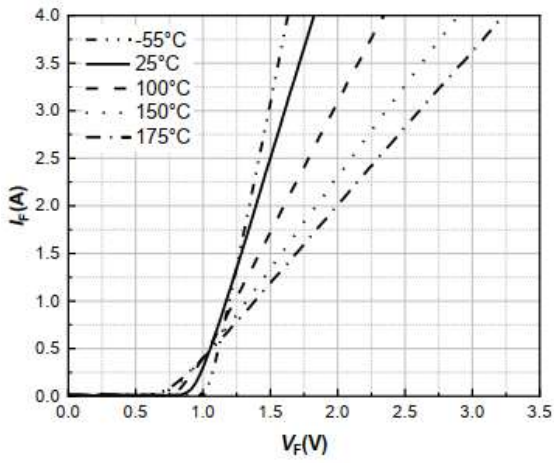


Figure 1. Forward characteristics

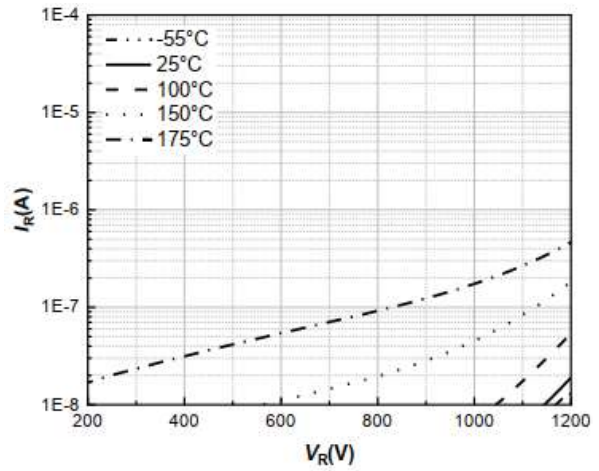


Figure 2. Reverse current as function of reverse voltage

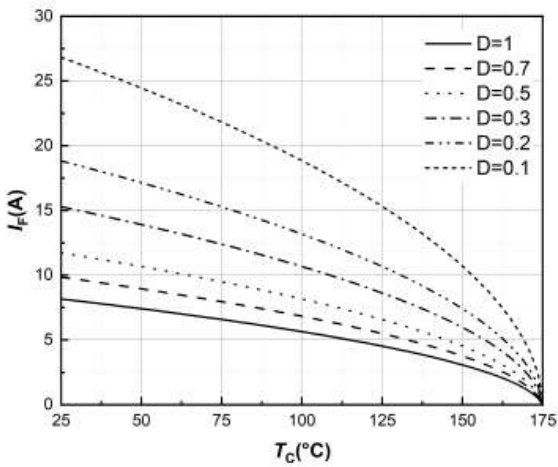


Figure 3. Diode forward current as function of temperature, D=duty cycle

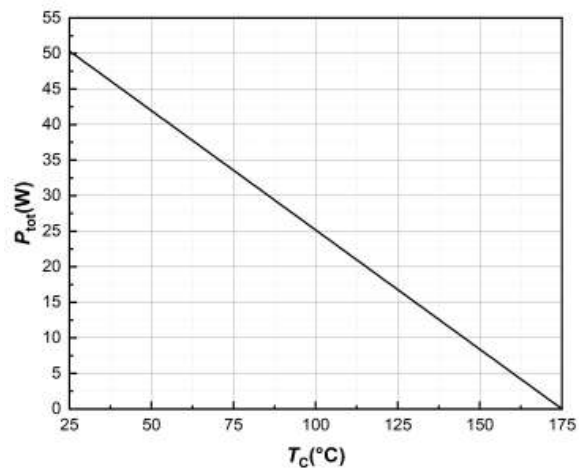


Figure 4. Power dissipation as function of case temperature

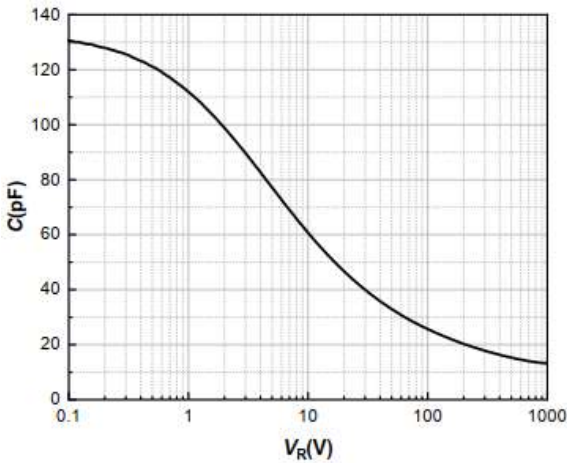


Figure 5. Capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25^\circ\text{C}$; $f=1\text{ MHz}$

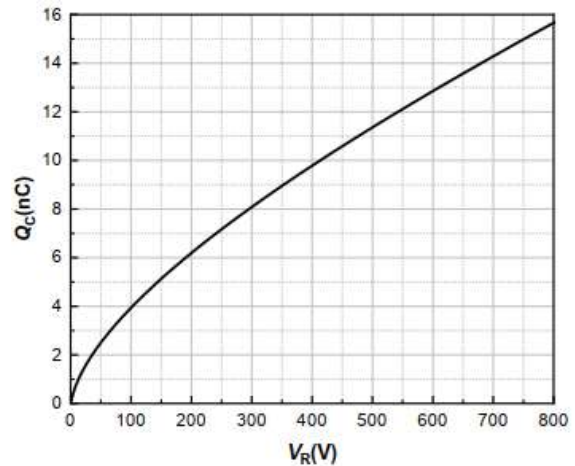


Figure 6. Reverse charge as function of reverse voltage

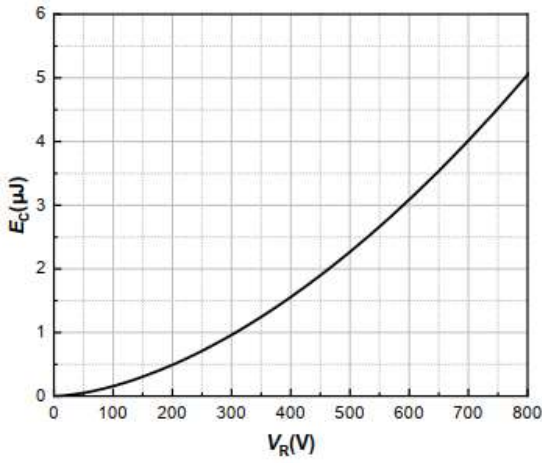


Figure 7. Capacitance Stored Energy

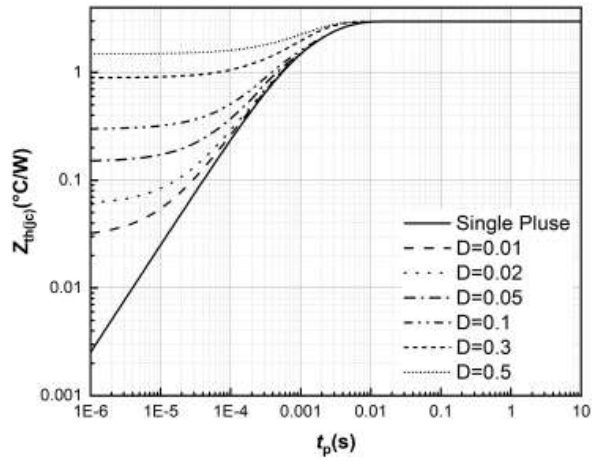
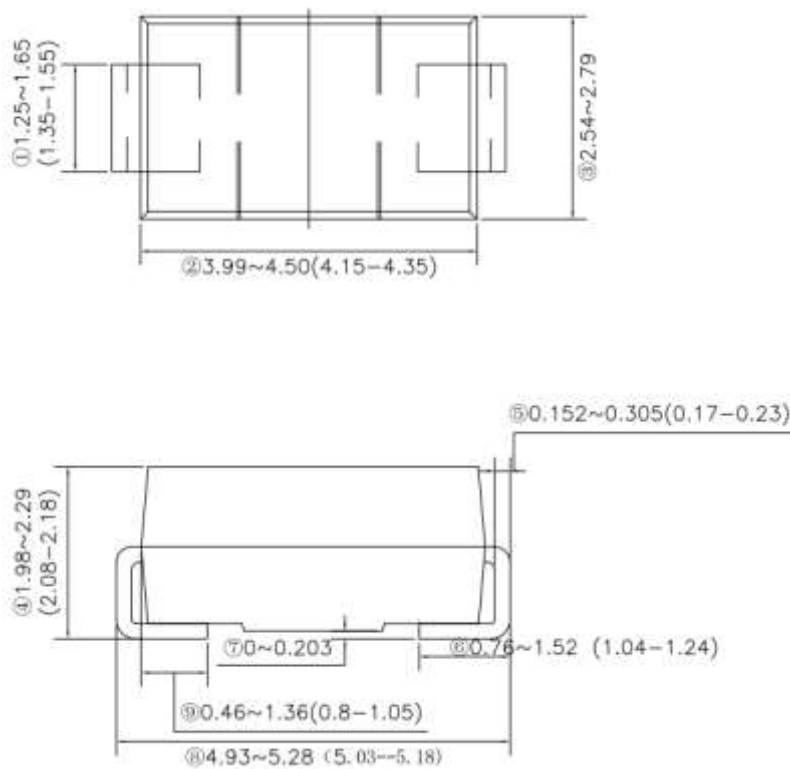


Figure 8. Max. transient thermal impedance, $Z_{th(jc)} = f(t_p)$, parameter: $D = t_p/T$

• SMA Package outlines : Dimensions in (mm)



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